

isc N-Channel MOSFET Transistor

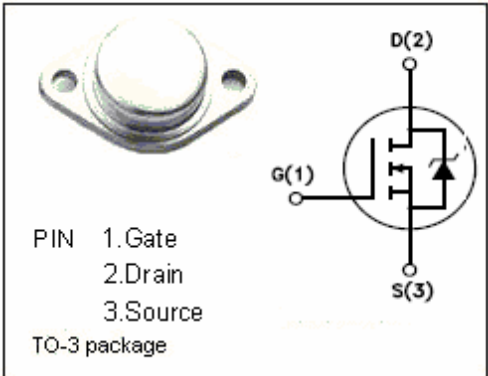
IRF470

DESCRIPTION

- Repetitive Avalanche Ratings
- Dynamic dv/dt Rating
- Hermetically Sealed
- Simple Drive Requirements
- Ease of Paralleling

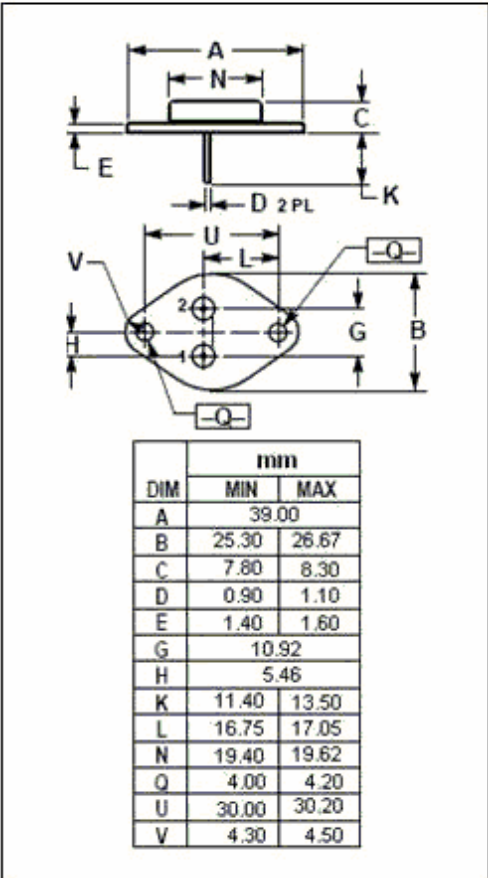
APPLICATIONS

- Designed for applications such as switching power Supplies ,motor controls ,inverters ,choppers ,audio amplifiers and high energy pulse circuits.



ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	ARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage (V _{GS} =0)	500	V
V _{GS}	Gate-Source Voltage	± 20	V
I _D	Drain Current-continuous@ TC=25°C	24	A
P _{tot}	Total Dissipation@TC=25°C	300	W
T _j	Max. Operating Junction Temperature	-55~150	°C
T _{stg}	Storage Temperature Range	-55~150	°C



THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance,Junction to Case	0.42	°C/W
R _{th j-A}	Thermal Resistance,Junction to Ambient	30	°C/W

isc N-Channel Mosfet Transistor**IRF470****• ELECTRICAL CHARACTERISTICS (T_C=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0; I _D = 0.25mA	500			V
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D = 0.25mA	2		4	V
R _{DS(ON)}	Drain-Source On-stage Resistance	V _{GS} = 10V; I _D = 12A			0.23	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = ±20V; V _{DS} = 0			±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 500V; V _{GS} = 0			250	uA
V _{SD}	Diode Forward Voltage	I _F = 24A; V _{GS} = 0			1.8	V